Amendments to the Claims

Claims 1-96 (Cancelled).

97. (Currently amended) A method for forming a low dielectric constant insulative structure disposed between a pair of conductive lines comprising:

providing the pair of conductive lines over a substrate, the conductive lines each having an upper surface;

forming a mass of a material over the substrate, the mass disposed over and between the pair of conductive lines, the material comprising a mixture of a first material that is substantially vaporizable in an oxidizing atmosphere and a second material that is substantially non-vaporizable in an oxidizing atmosphere;

planarizing the mass to a level about equal to the upper surfaces of the pair of conductive lines;

depositing a layer of insulative material; and

vaporizing at least a portion of the mass disposed between the conductive lines to form the low dielectric constant insulative structure therebetween, the structure comprising at least one void.

98. (Cancelled).

99. (Currently amended) The method of Claim 97 ~~114~~ wherein ~~providing a~~ the first material ~~comprising a mixture~~ comprises ~~providing a mixture of a~~ carbon, and the second ~~comprising~~ material ~~and a~~ comprises silicon oxide ~~material~~.

100. (Currently amended) The method of Claim 97 ~~114~~ wherein the ~~providing a material comprising a~~ mixture comprises ~~providing a mixture of~~ carbon and SiC_x, where "x" is a number between about 0.2 and 1.5.

101. (Currently amended) The method of Claim 97 ~~113~~ wherein forming a mass of material comprises forming the mass by plasma decomposition of a hydrocarbon or halogen substituted hydrocarbon.

102. (Currently amended) The method of Claim 101 ~~117~~ wherein forming the mass by plasma decomposition comprises forming a porous carbon mass.

103. (Currently amended) The method of Claim 97 ~~113~~ wherein depositing a layer of an insulative material comprises depositing the layer prior to vaporizing the mass.

104. (Currently amended) The method of Claim 97 ~~113~~ wherein forming a layer of an insulative material comprises forming a silicon oxide layer having a thickness of about 500 Angstroms.

105. (Currently amended) The method of Claim 104 ~~120~~ wherein forming a silicon oxide layer comprises forming the layer by sputter deposition of silicon dioxide.

106. (Currently amended) The method of Claim 97 ~~113~~ wherein forming a layer of an insulative material comprises forming the layer after vaporizing the mass.

107. (Currently amended) The method of Claim 97 ~~113~~ wherein forming a mass of material comprises forming the mass of a material comprising about 20% to about 80% SiC_x, where "x" is a number from about 0.2 to about 1.5.